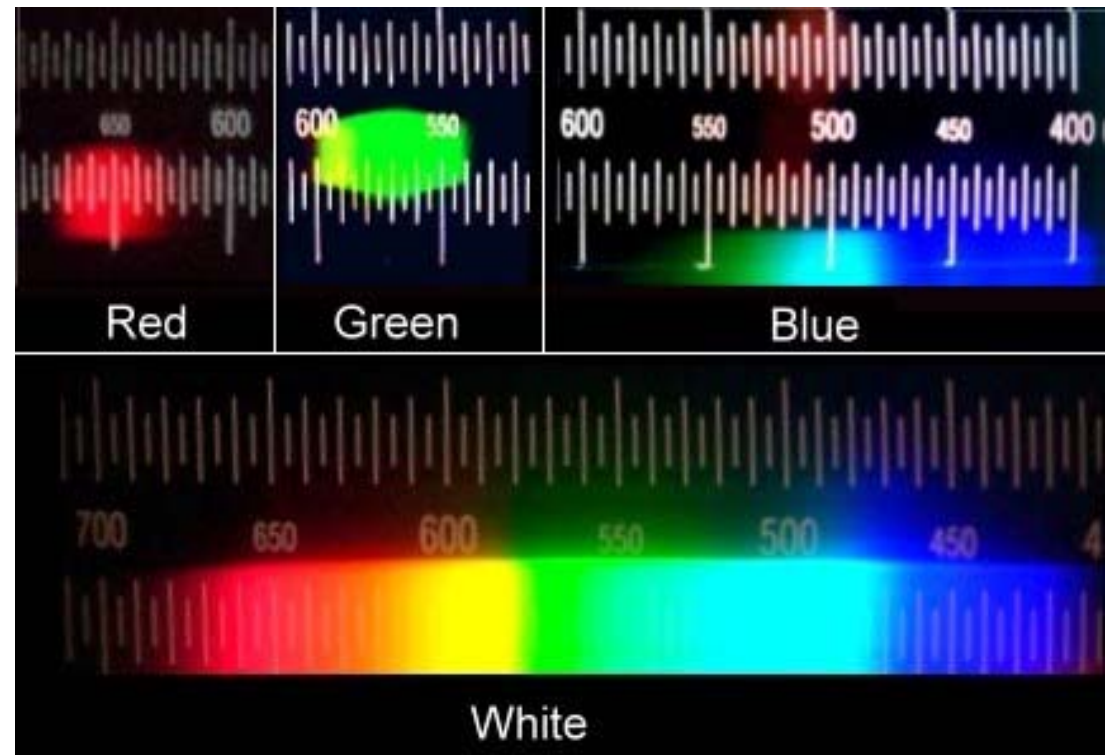

UV Beschichtungen

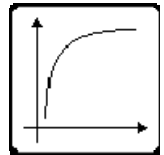
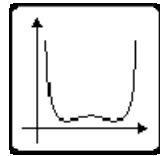
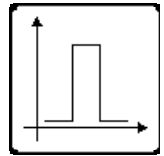
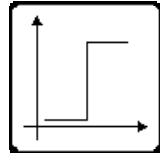
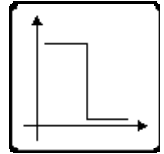
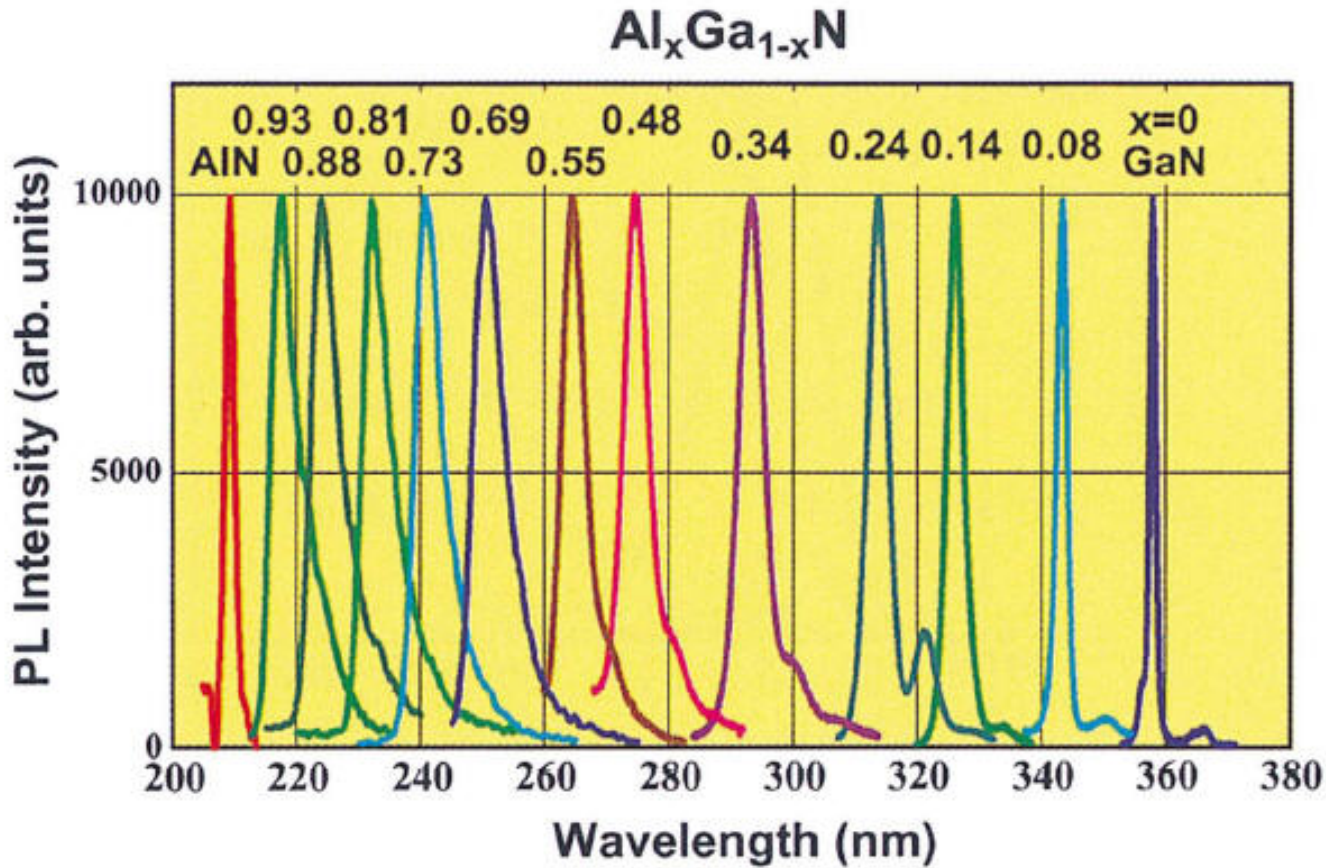
Norbert Kaiser

27. November 2008

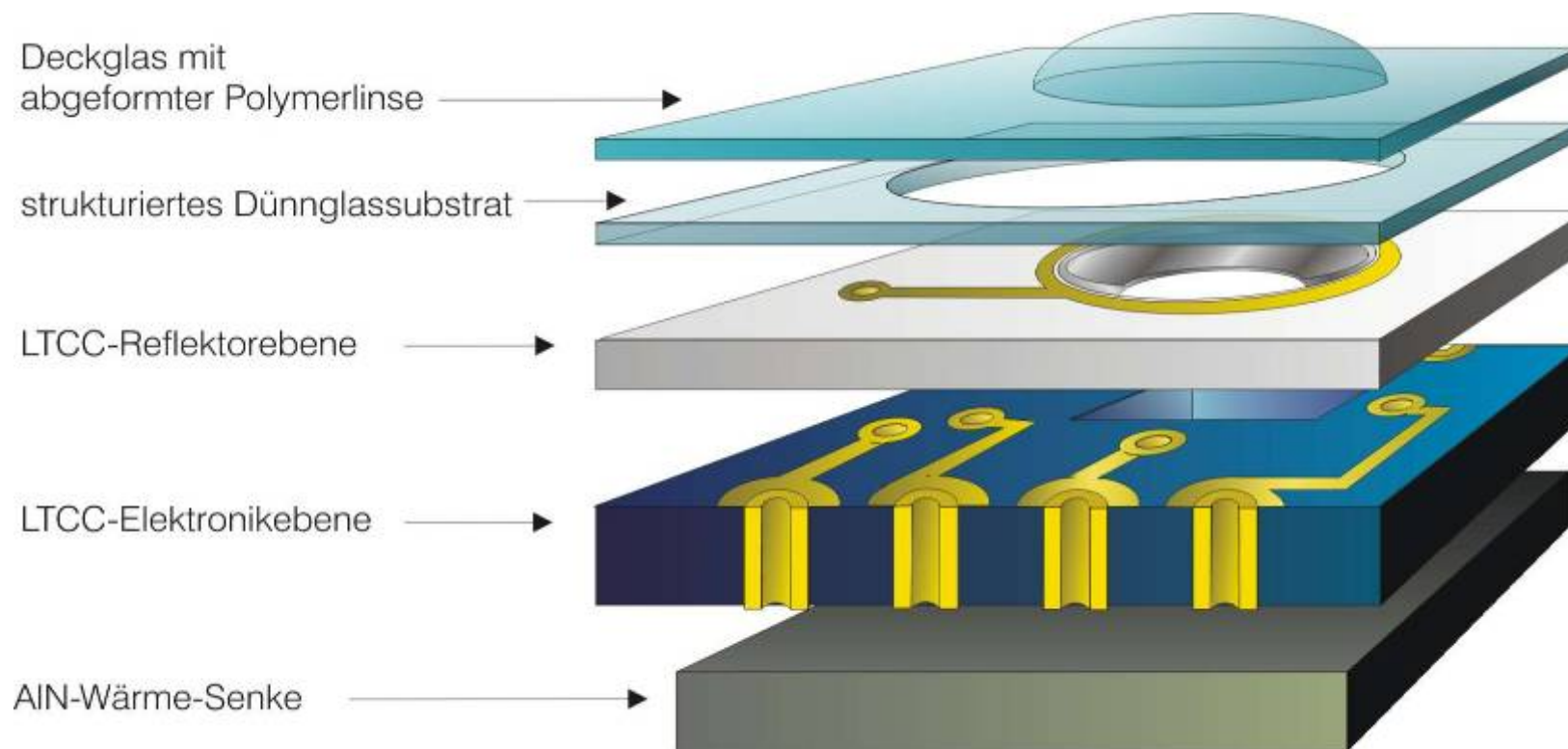
Mainz



UV Beschichtungen - Wellenlängen



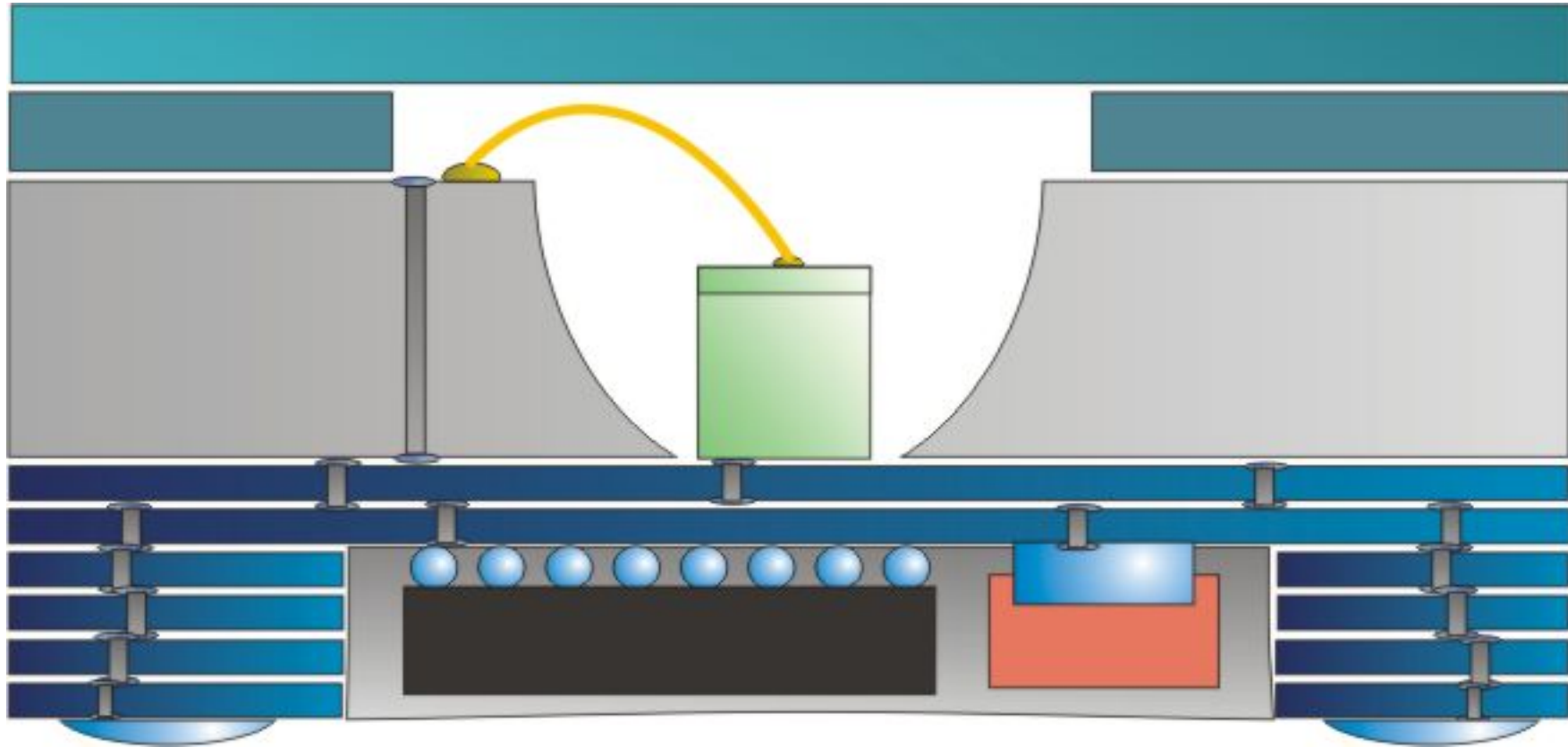
Qualifikation von Glaskeramik (LTCC) für Optische und Optoelektronische Anwendungen



Design-Skizze zu einem Beleuchtungsmodul auf LTCC-Basis

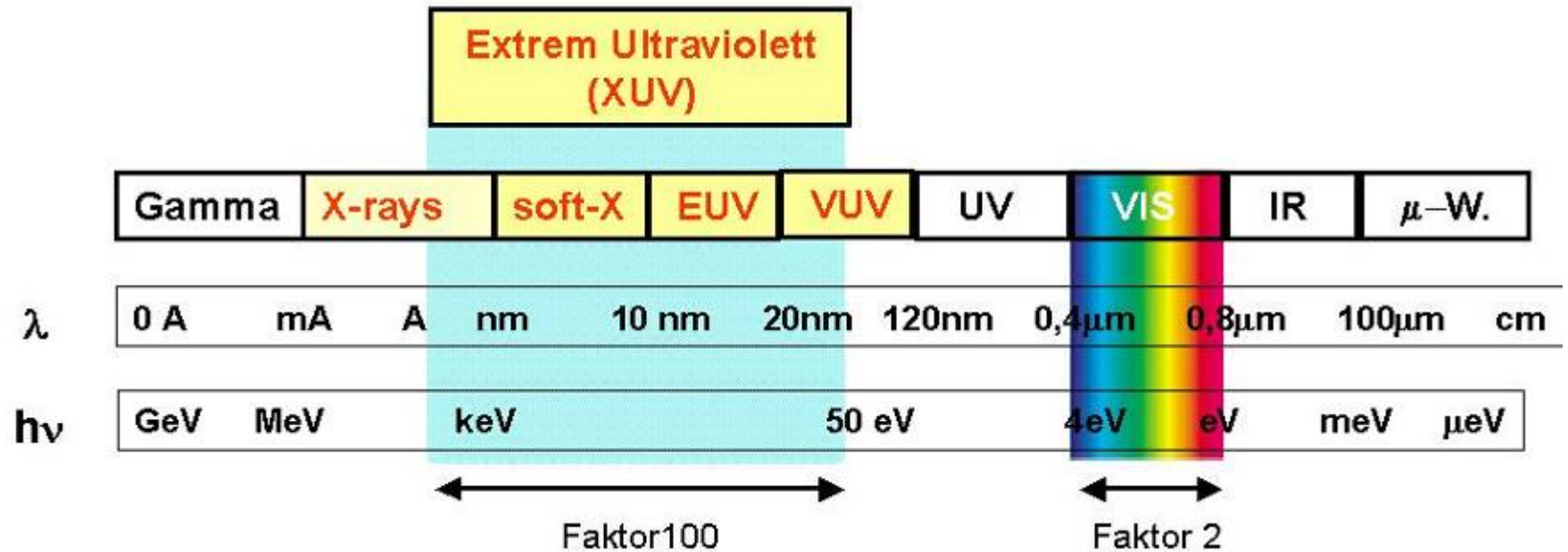
SchichtUV1

Optoelektronischer Demonstrator - LED-Beleuchtungsmodul -



SchichtUV1

XUV

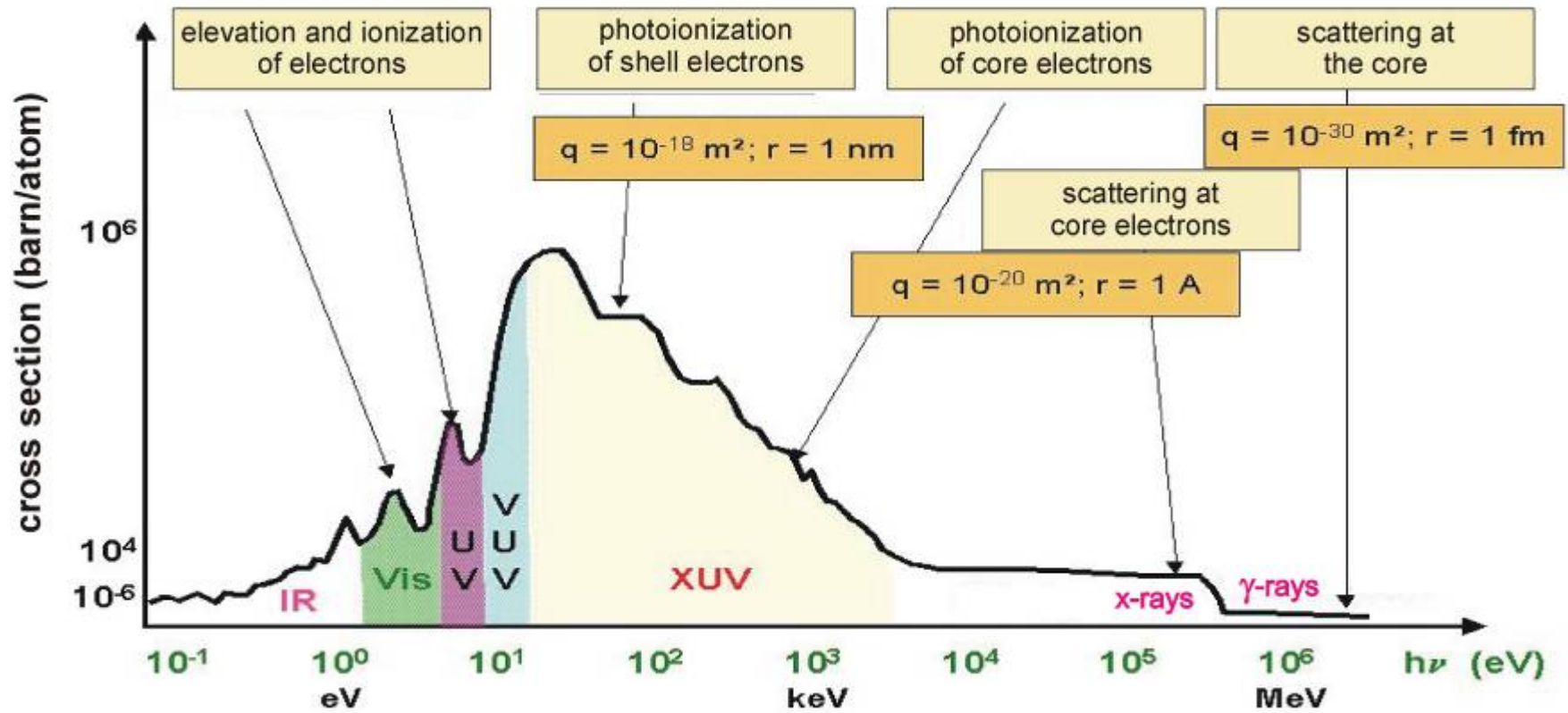


- DUV - Deep UltraViolet: 200 nm – 280 nm
- VUV - Vacuum UltraViolet: 100 nm – 200 nm
- XUV – Extreme UltraViolet: 1 nm - 100 nm
- EUV – Lithography Extreme UltraViolet: around 13 nm

SchichtUV1



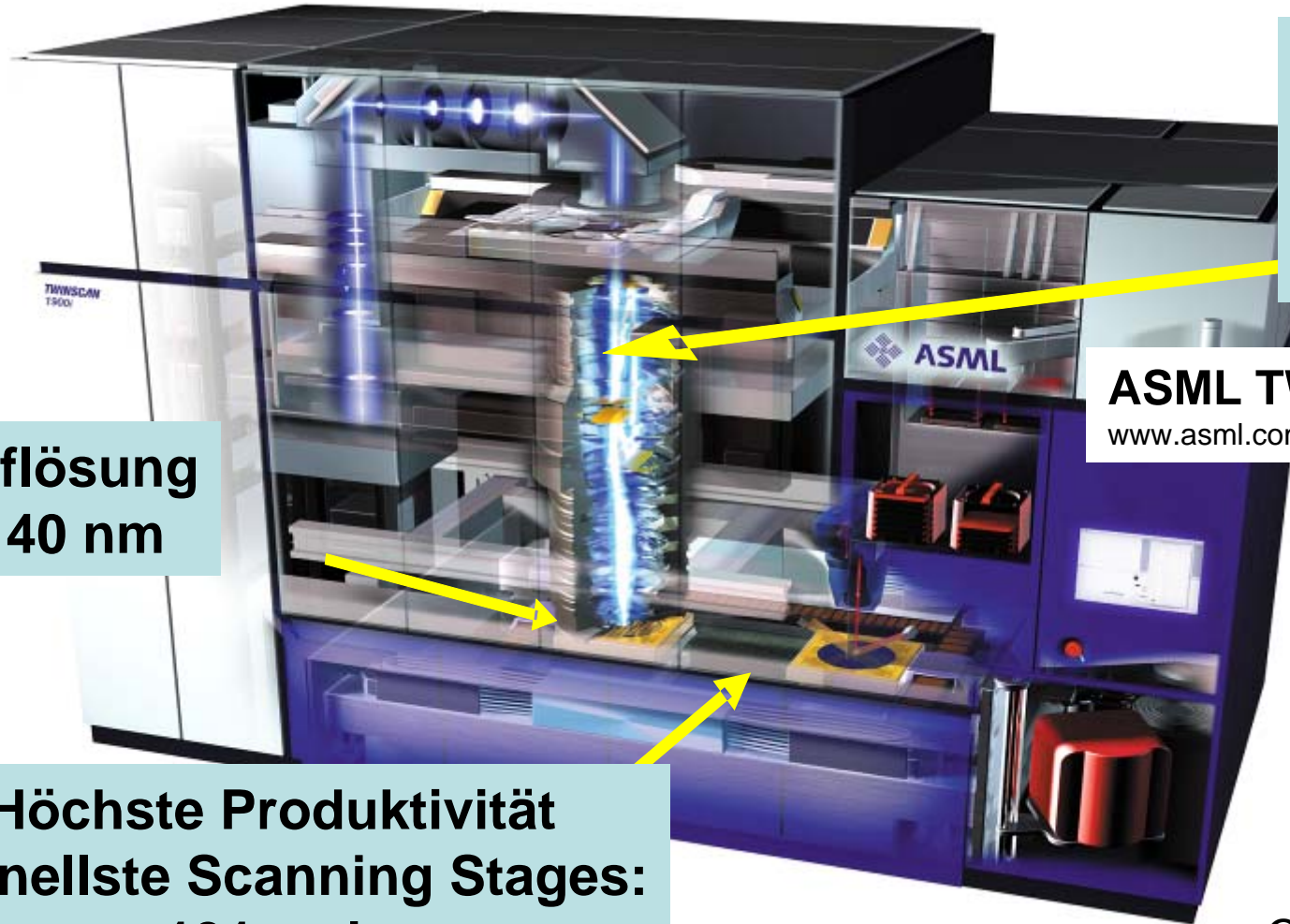
XUV



Innovationen durch kurze Wellenlängen:

- DUV-, EUV- Lithographie
- Mikroskopie im "Wasserfenster" ($\lambda = 2.3 \text{ nm} - 4.4 \text{ nm}$)
- Astronomie ($\lambda = 5 \text{ nm} - 50 \text{ nm}$)
- Spektroskopie, Plasmaanalytik
- XUV Laser
- Desinfizieren
- Trocknen, Härten

Der Waferscanner/stepper der neuesten Generation ist die...



193 nm
Höchste NA 1.35
ArFi katadioptrisches
Objektiv

ASML TWINSCAN™ XT:1900Gi
www.asml.com

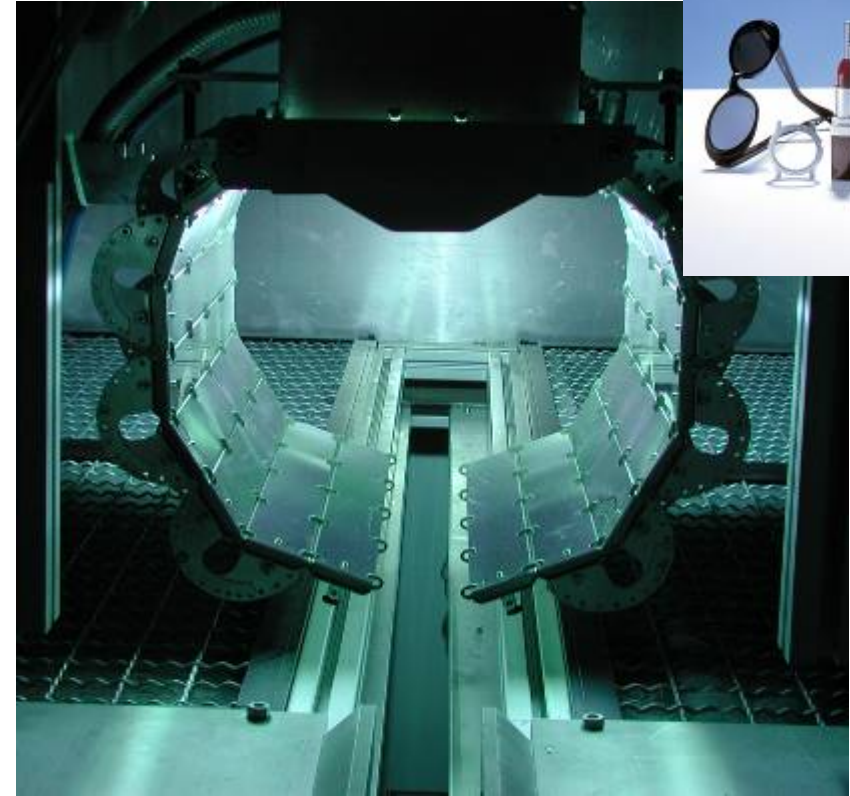
Auflösung
≤ 40 nm

Höchste Produktivität
Schnellste Scanning Stages:
131 wph
@ 125 Belichtungen / Wafer

Quelle: Christoph Zaczek

... Schlüsseltechnologie in der Halbleiterfertigung

Empfänger



Photochemische Polymerisation

Quelle: Oliver Treichel

E

Serienproduktion

- 10 Kilometer Reflektorprofil pro Jahr

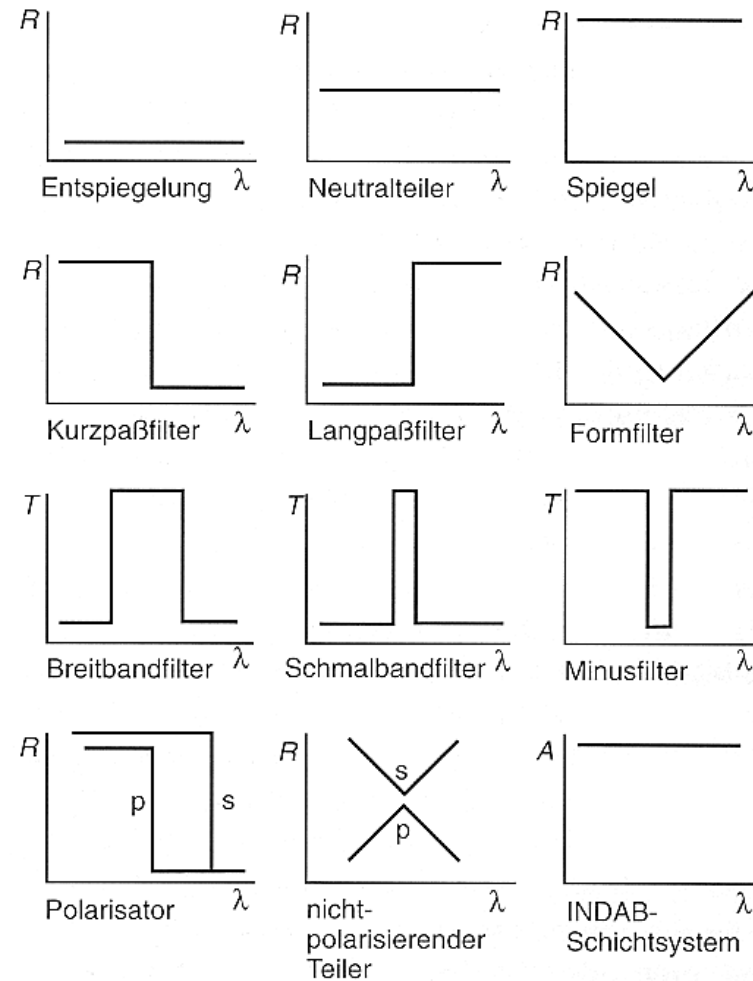


Quelle: Oliver Treichel

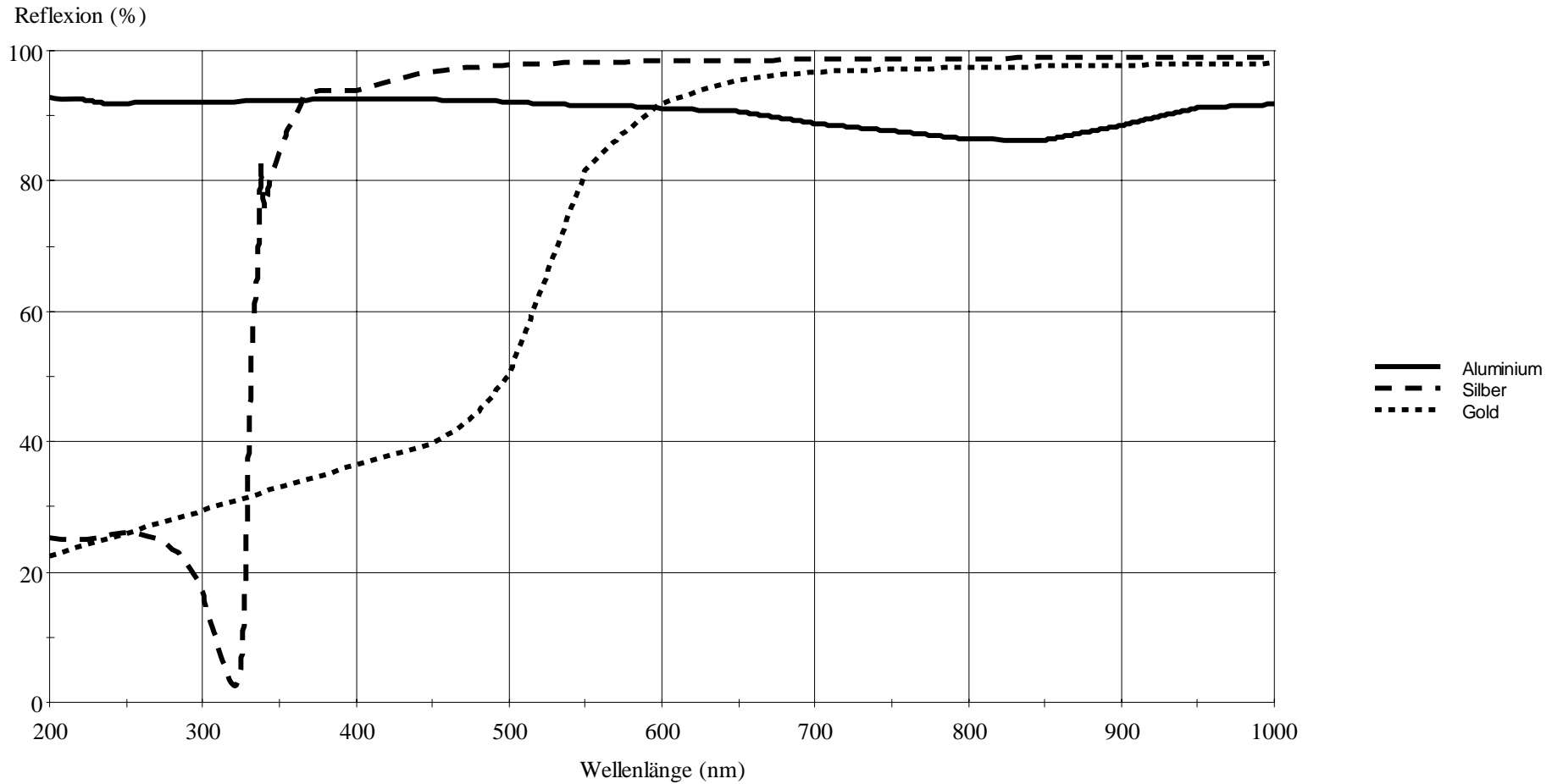
Definition

Dünne optische Schicht

- dient zum Einstellen der optischen Eigenschaften (Reflexion, Transmission, Absorption) einer Oberfläche
- Funktion beruht auf dem Interferenzeffekt und/oder den intrinsischen Eigenschaften (Absorption) der Schicht- und Substratmaterialien
- Zusatzfunktionen: Kratz-, Umwelt-, Strahlungsschutz, Dekoration, ...

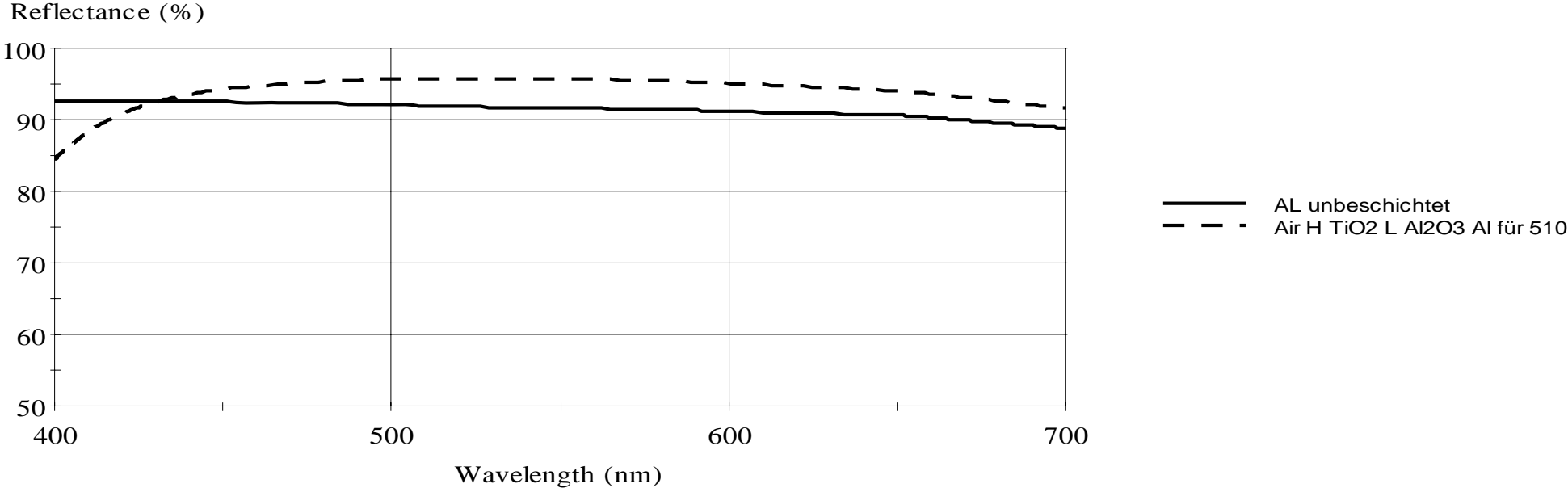


Spiegel - Metallspiegel



Spiegel – metall-dielektrische Spiegel

verstärktes Al



SchichtUV1

HR for the XUV /FUV/VUV region (50 – 140 nm)

Application field:

Astrophysics,

Solar physics,

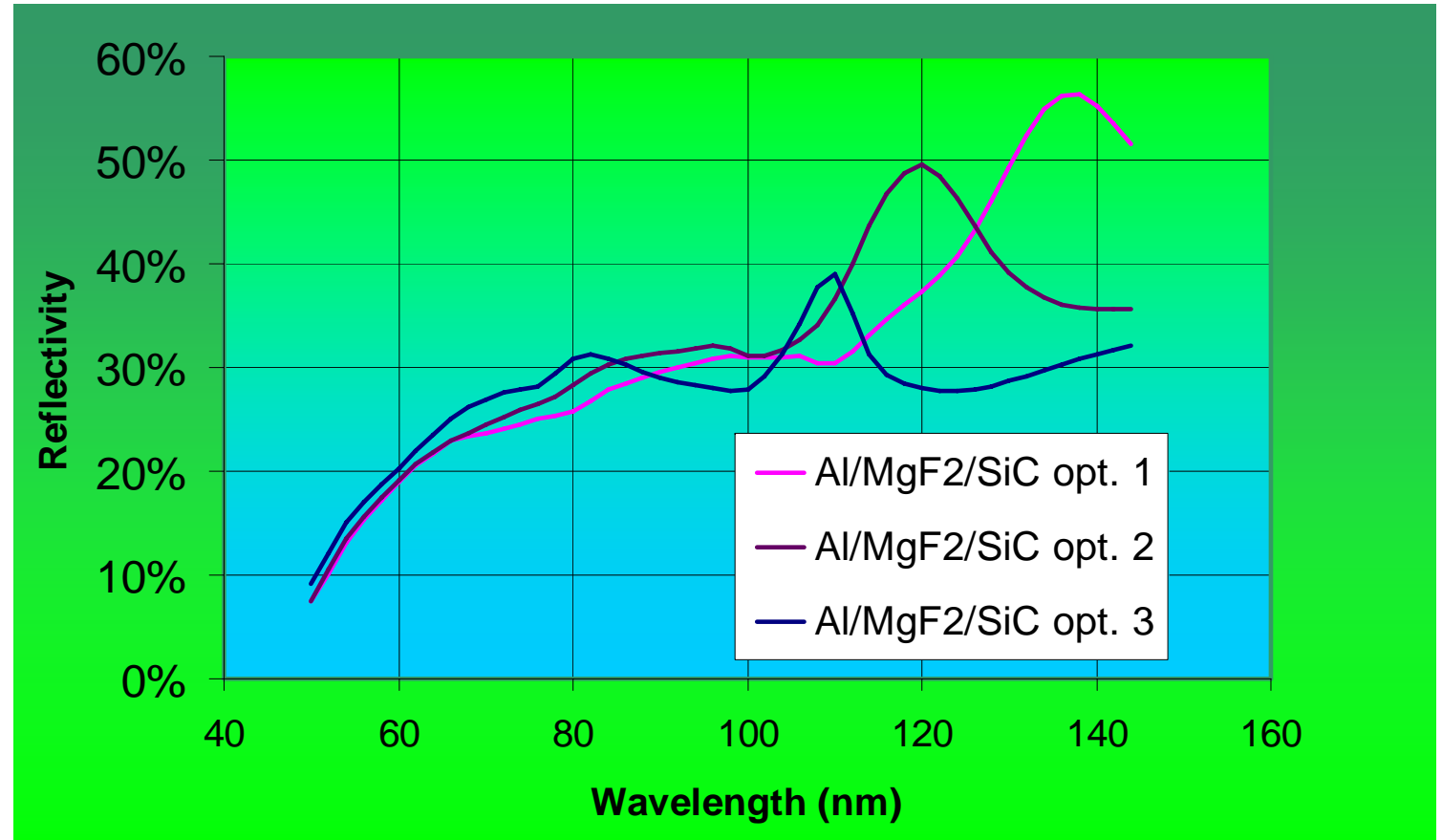
Atomosphere,

Hot plasma

Alu + Bilayers :

Al + MgF₂ + ...

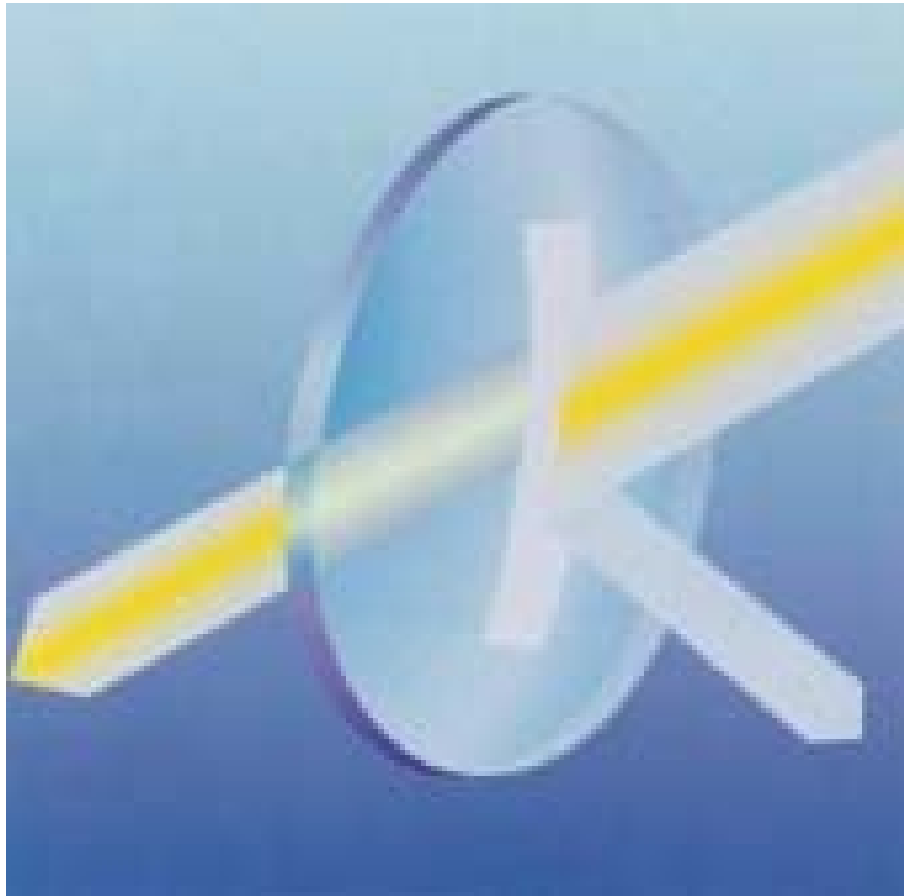
SiC, B₄C, Si₃N₄, Ir, Mo, Si....



Best record worldwide@ 90 nm : 34%,

IOF result @ 90 nm :32% (recently measured by PTB BESSY II)

Reflexion

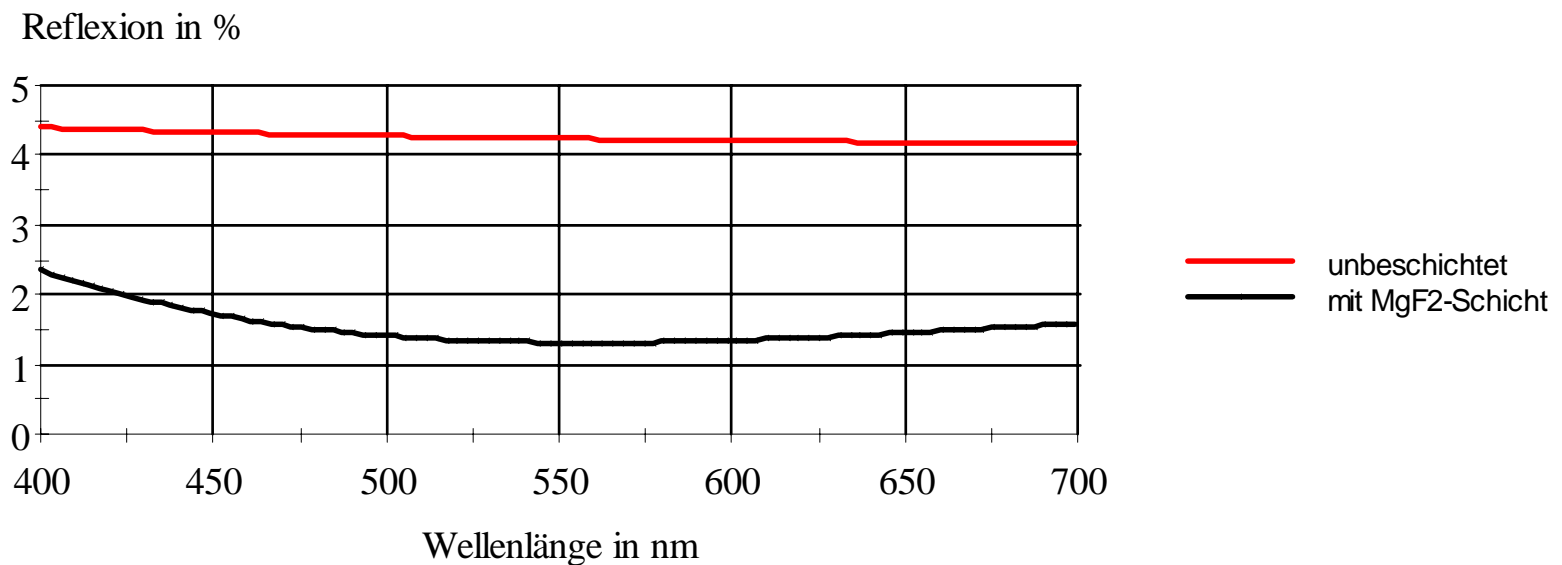


Fraunhofer Institut
Angewandte Optik
und Feinmechanik

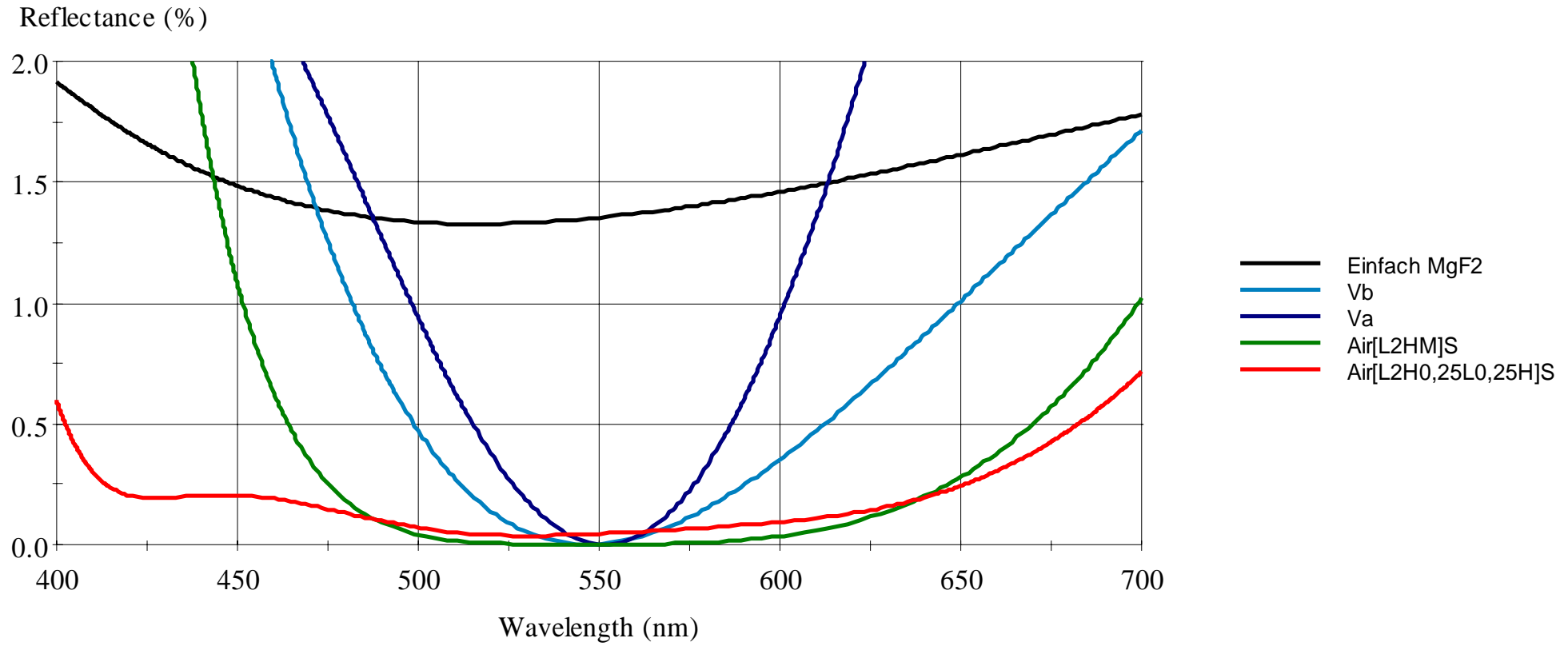


Design optischer Schichtsysteme

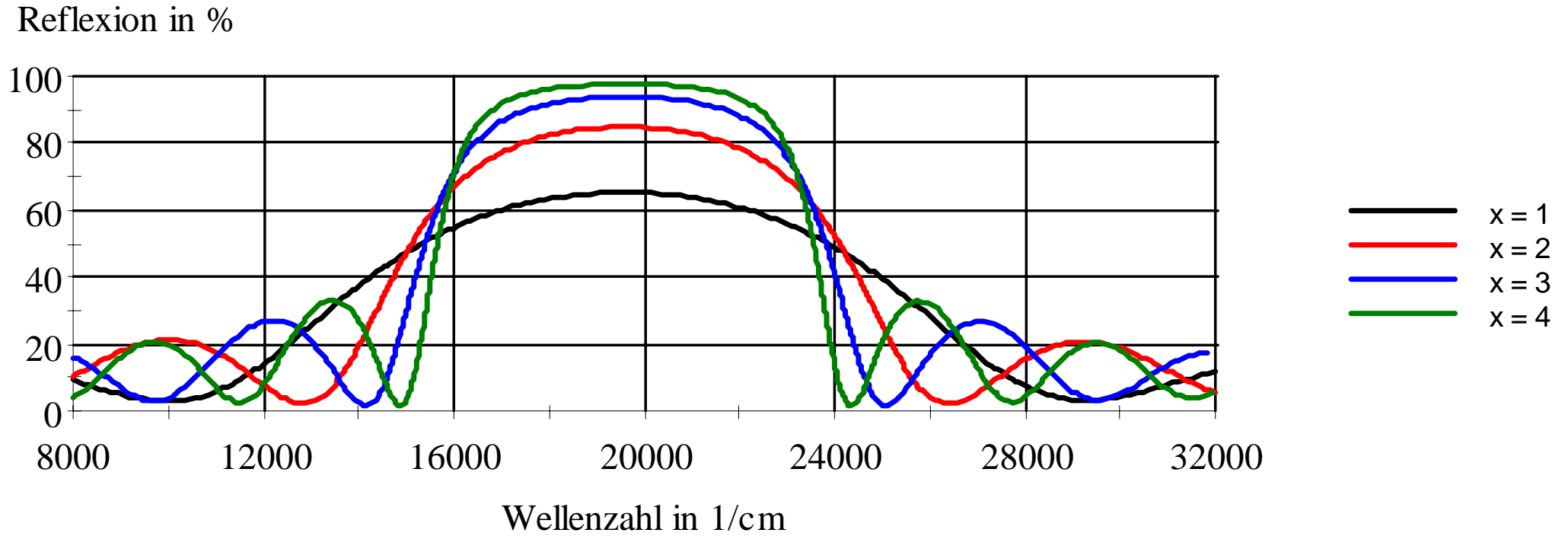
$$d_{\lambda/4} = \frac{\lambda}{4} \frac{1}{n_{\text{MgF}_2}} = \frac{550\text{nm}}{4} \frac{1}{1,38} = 99,64\text{nm} \quad (4)$$



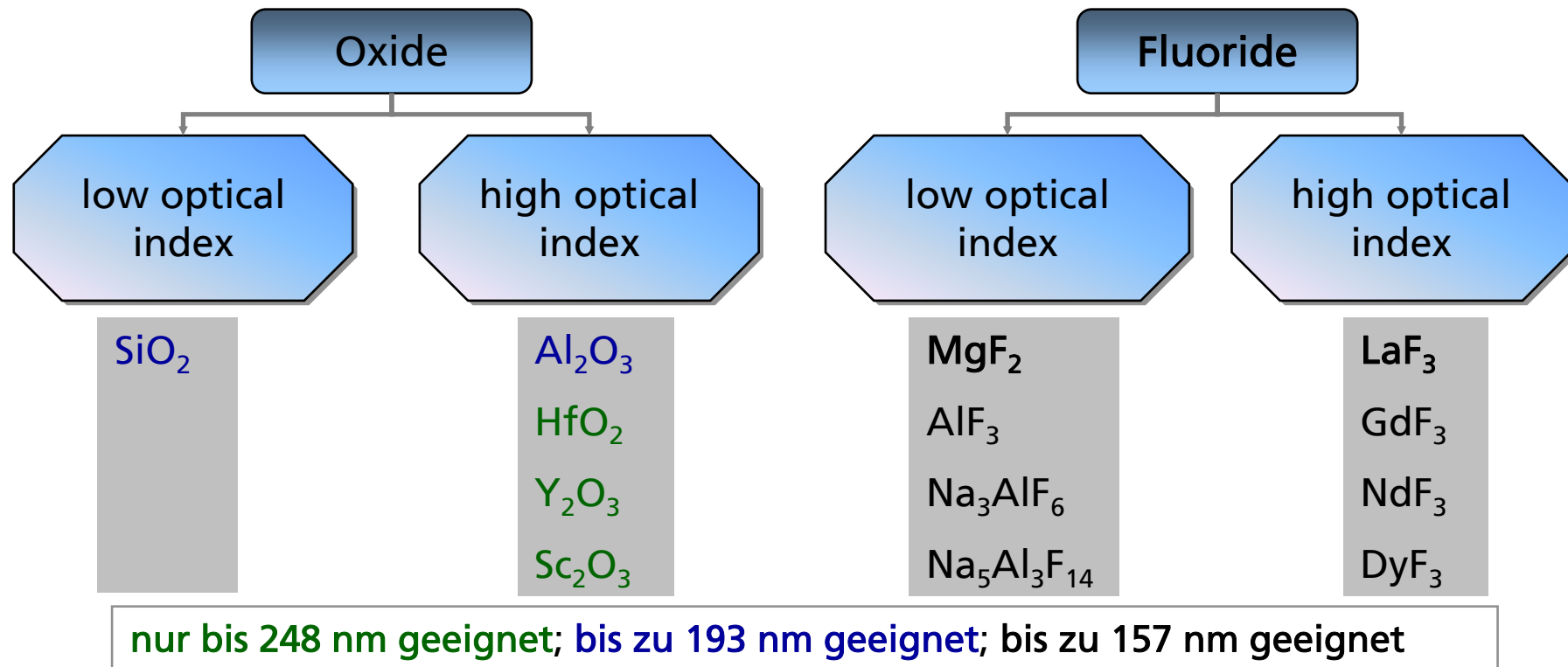
Spektrale Reflexion einer Glasoberfläche ohne und mit $\lambda/4$ -MgF₂-Schicht für senkrechten Lichteinfall ($\lambda_0=550\text{nm}$).



Spiegel – dielektrische Spiegel



Schichtmaterialien für DUV / VUV – Lithographie

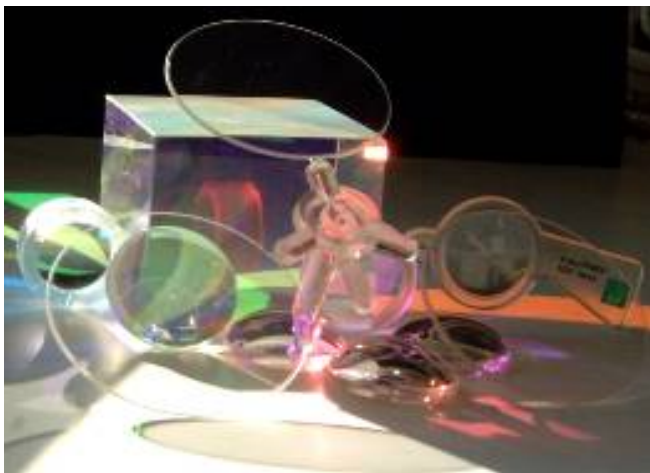


- begrenzte Auswahl geeigneter Materialien
- Brechzahlkontrast (niedrig- und hochbrechendes Material) gering
⇒ höhere Schichtzahl notwendig; schmalbandige Designs

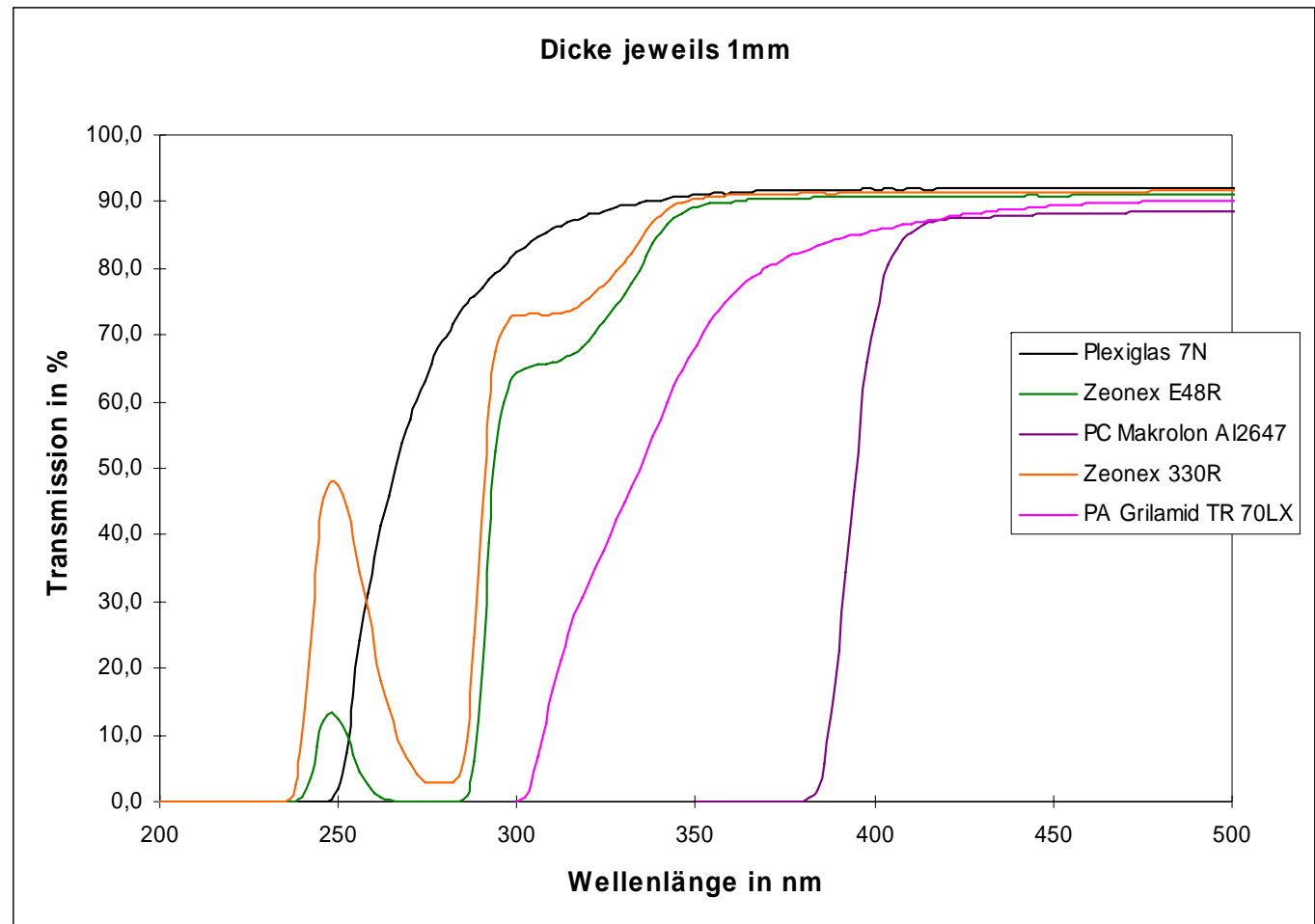
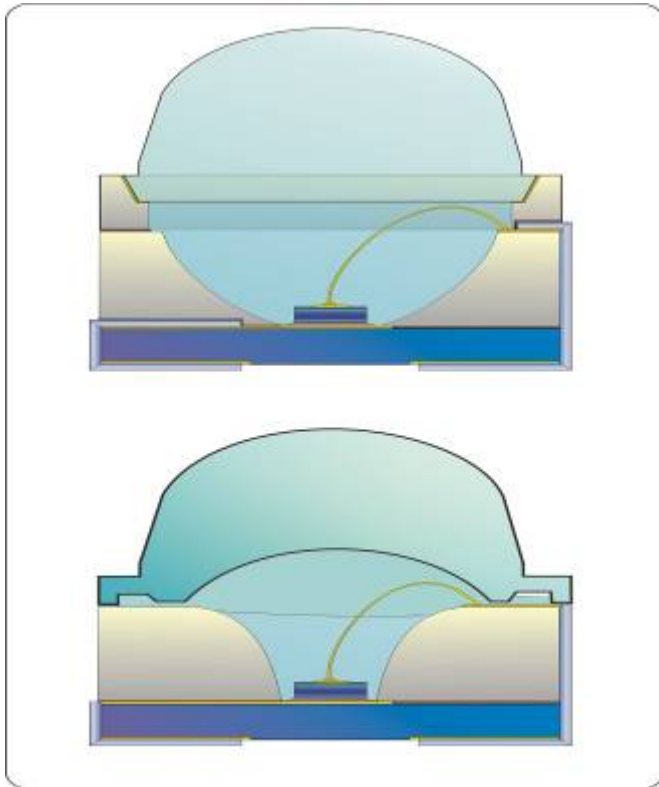




Coating on plastics

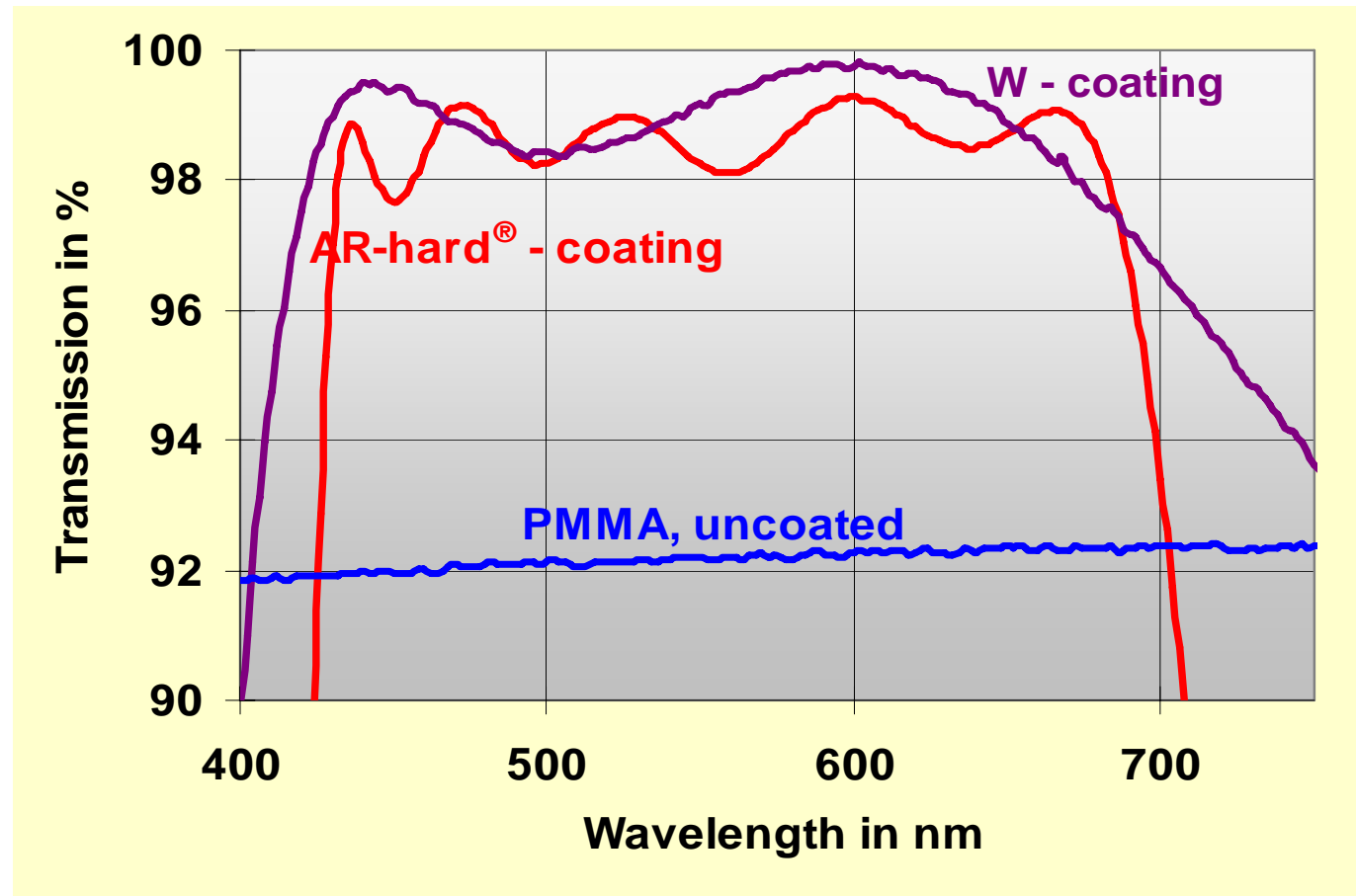


Coating on plastics



Antireflective coating for PMMA

- „W-coating“ or scratch-resistant coating AR-hard®
- APS -technology
- 2005-2007
5 license agreements

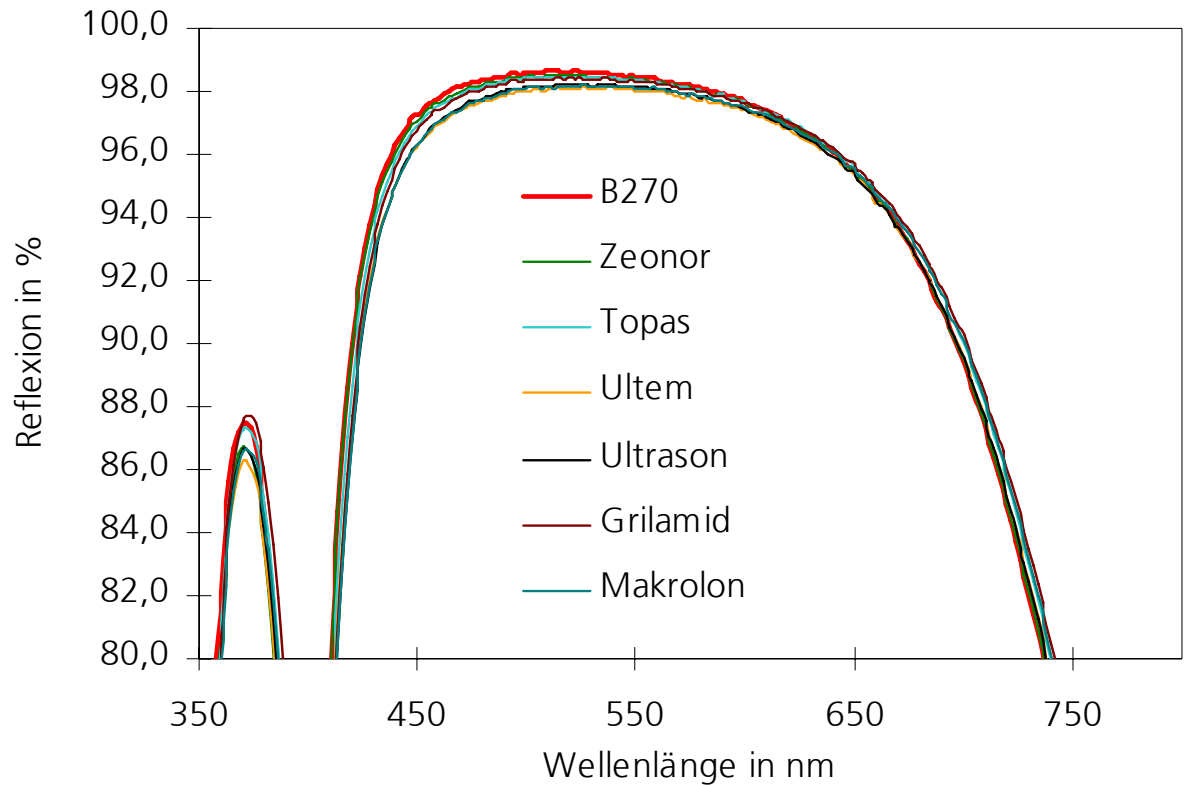


Patent DE 10201492A1



High reflective coating for plastic optics

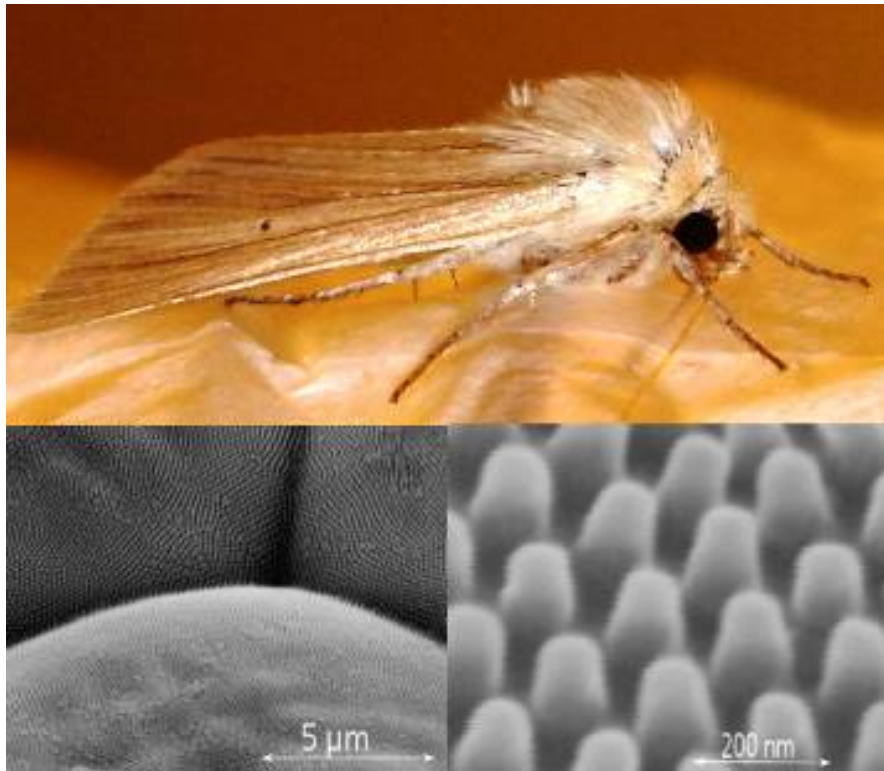
- Al and Ag-mirrors with high adhesion on various polymers
- Dielectric layers enhance optical properties and environmental stability



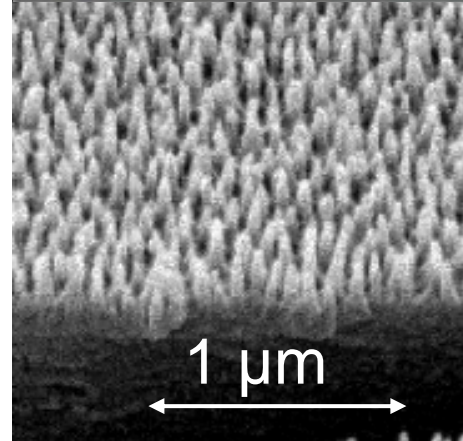
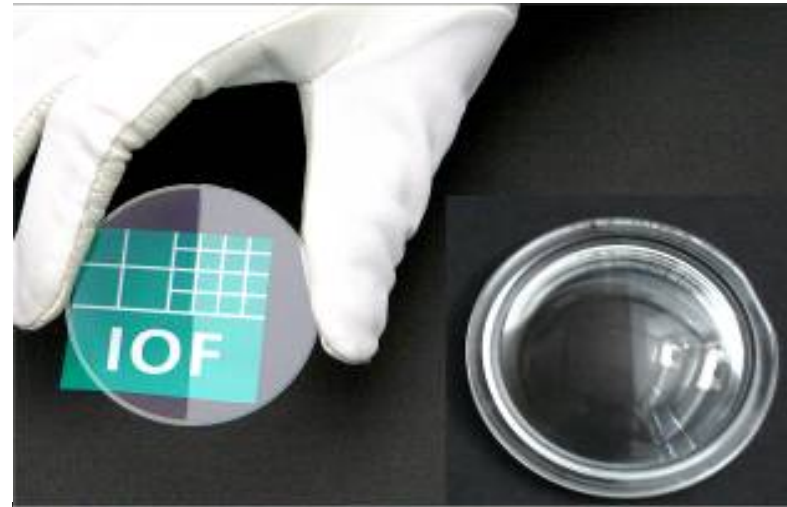
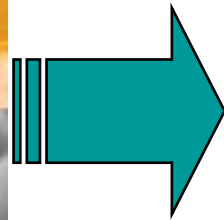
Enhanced Al-mirrors on various polymers and optical glass, $R(\text{VIS}) > 97\%$

Project REBEKA, 2004-2007, FKZ: B409-04005

Stochastic antireflective structures AR-plas



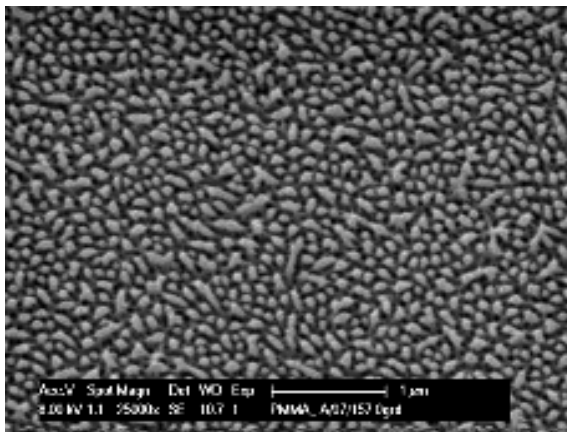
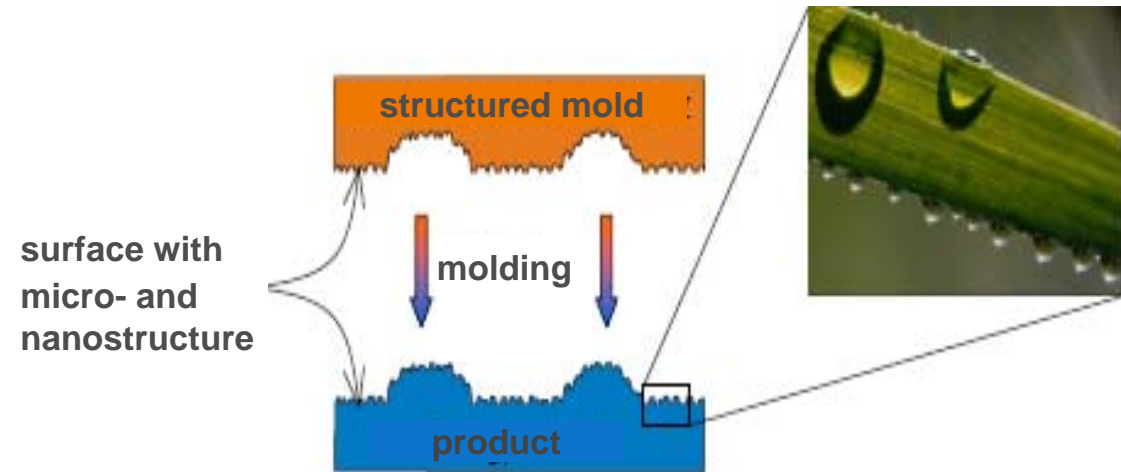
Antireflective structure on moth eye



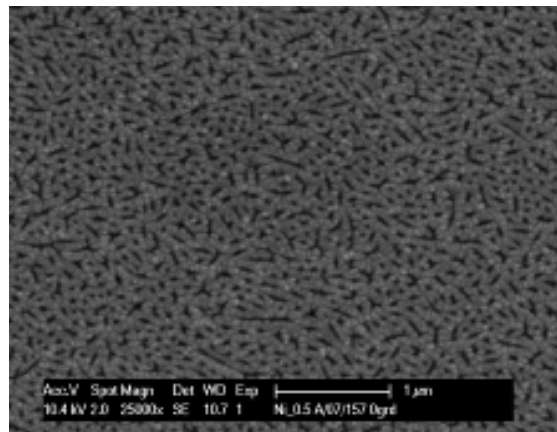
Antireflective structure on PMMA produced by plasma etching

NanoReplica- Nanoprecise mold-fabrication and replication

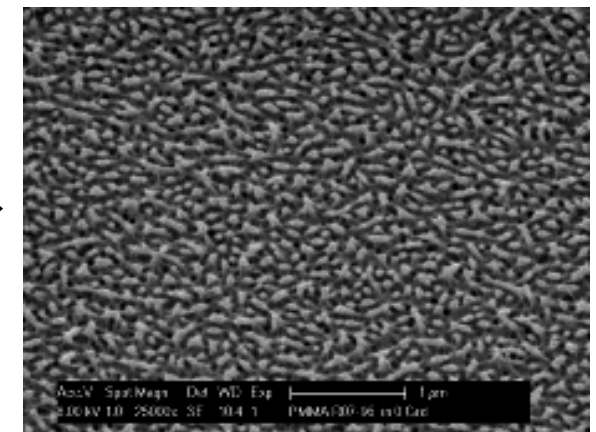
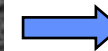
- Joint project: 09/2006 - 08/2010
- Direct Functionalisation by injection molding or hot-embossing of micro- and nanostructures
- Special task: replication of stochastic antireflective structures



PMMA- master with positiv AR- structure

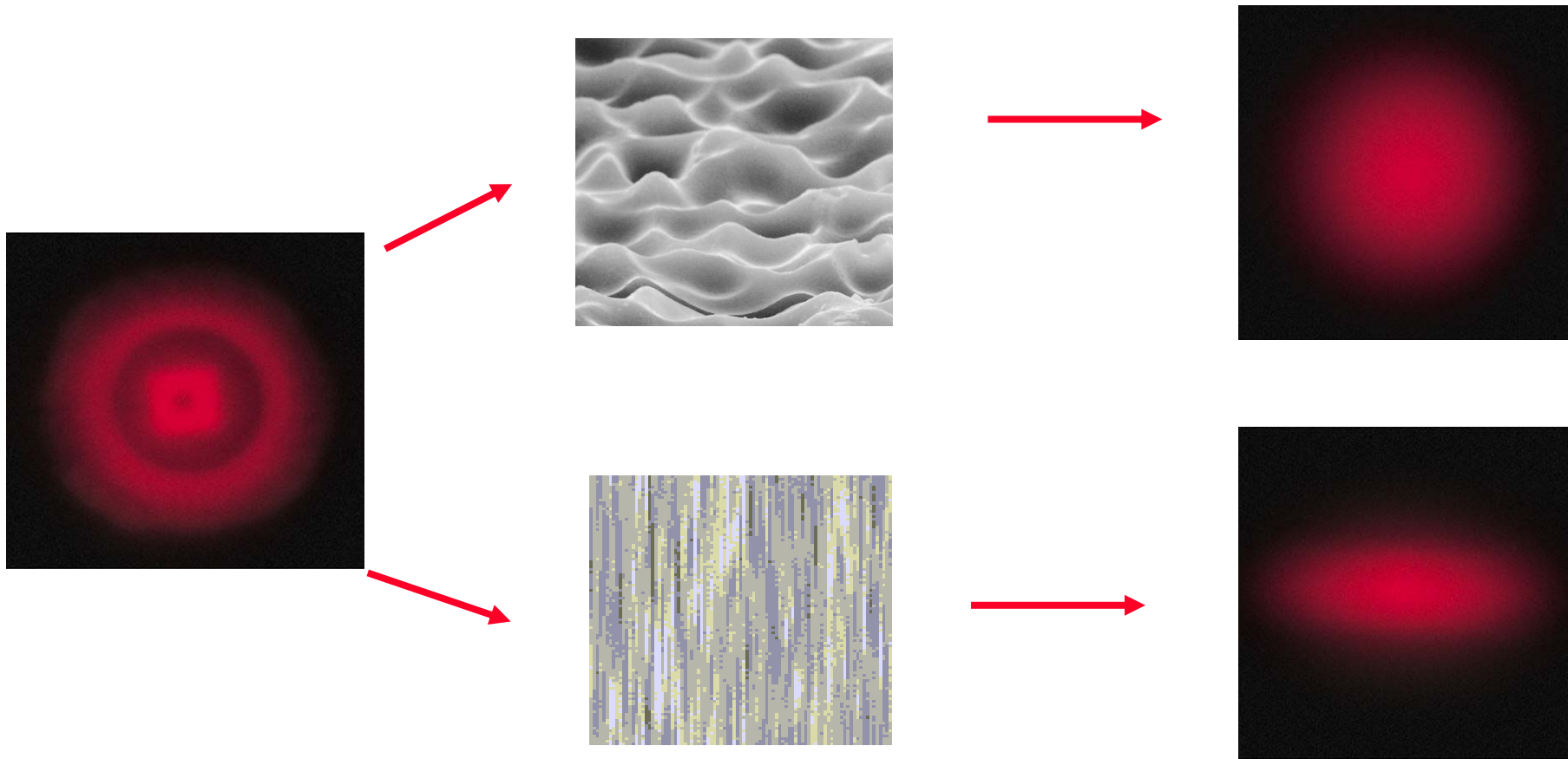


Ni- stamp with negativ structure



patterned PMMA- replica with positiv AR- structure

- Optik : effiziente Lichtauskopplung
Strahlformung



Johann Wilhelm Ritter (1776 – 1810)



- Geb. 16. Dezember 1776 in Samitz
- Deutscher Physiker und Philosoph der Frühromantik
- Ab April 1796 Student in Jena
- 1802 Entdeckung der UV Strahlung in Jena
- Gest. 23. Januar 1810 in München

Tailored Light - Licht nach Maß

Fraunhofer
Institut
Angewandte
und Feinoptik

Thank you for your attention